LITE-ON LITEON SEMICONDUCTOR

SILICON CARBIDE SCHOTTKY DIODE

LSC10065Q8

- 650 Volts

DFN8080

MAX

1.10

1.10

0.05

8.10

7.30

8.10

4.85

2.85

0.50

0.60

MIN

0.90

0.90

0.00

7.90

7.10

7.90

4.65

2.65

0.30

0.40

All d mension in millimeter

0.20 REF

2.0 BSC

- 10 Amperes

REVERSE VOLTAGE

D1

٩ 2

PIN 3.4

FORWARD CURRENT

5

PIN 5

DFN8080

DIM

Α

b

b1

С

D

D1

F

E1

E2

E3

е

L

FEATURES

- · Positive temperature coefficient for safe operation and easy of paralleling
- 175°C maximum operating junction temperature
- Extremely fast switching not dependent on temperature
- · Essentially no reverse or forward recovery

APPLICATION

- Power converters
- Switching-mode power supplies
- Power Factor correction modules

MECHANICAL DATA

- Case: DFN8080 molded plastic
- · Case Material: "Green" molding compound, UL flammability classification 94V-0,(No Br. Sb. Cl.) "Halogen-free".
- Moisture Sensitivity Level 3 per J-STD-020
- · Lead free finish, RoHS compliant
- Weight: 0.214 grams (Approximate)
- Marking code: LSC10065Q8

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ABSOLUTE RATINGS

ABSOLUTE RATINGS							
PAR/	AMETER		SYMBOL	VALU	VALUE		
Maximum repetitive peak reverse voltage			VRRM	650		V	
Maximum DC blocking voltage			V _{DC}	650		V	
Maximum Average rectified output current @T _c =105°C			I _(AV)	10	10		
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load.			IFSM	40		А	
Operating junction and Storage Temperature range			TJ, TSTG	-55 ~ +175		°C	
STATIC ELECTRICAL CI	HARACTERIST	ICS					
PARAMETER	TEST C	TEST CONDITIONS		ТҮР	MAX	UNIT	
Forward voltage (Note1)	I _F =10A	TJ=25°C TJ=175°C	VF	 2.21	1.70 2.25	V	
Reverse Leakage current	V _R =650V	TJ=25°C TJ=175°C	IR	 173	250 550	uA	
Typical junction capacitance (Note 2)			CJ	310		pF	
DYNAMIC ELECTRICAL CHARACTERISTICS							
PARAMCETER	TEST CONDITIONS		SYMBOL	TYP	ТҮР		
Total capacitive charge	V _R =400V,dI/dt=250A/us, I _F =10A		Qc	24		nC	
THERMAL CHARACTER	ISTICS						
PARAMETER			SYMBOL	TYP	ТҮР		
Typical thermal resistance (Note 3.4)			RthJc	3		°C/W	
		RthJ∟	4				
Note :					REV8 ,Jan-20)19, KTGR02	

300us pulse width, 2% duty cycle. (1)

(2) Measured at 1.0MHz and applied voltage of 1.0V DC.

Thermal resistance test performed in accordance with JESD-51. (3)

The unit mounted on copper heat sink (50mm x 50mm x 1.5mm) & Aluminum fin type heat sink (75mm x 100mm x 25mm) (4)





RATING AND CHARACTERISTIC CURVES LSC10065Q8





FIG.3 TYPICAL FORWARD CHARACTERISTICS



INSTANTANEOUS FORWARD VOLTAGE, (V)

FIG.5 TYPICAL REVERSE CHARACTERISTICS 1.E+02 T_J = 175°C INSTANTANEOUS REVERSE CURRENT, 1.E+01 $T_1 = 150^{\circ}C$ 1.E+00 Т_J =25°С (MA) 1.E-01 T_J =125°C 1.E-02 1.E-03 130 260 390 520 650 RATED PEAK REVERSE VOLTAGE, (V)



FIG.4 TYPICAL JUNCTION CAPACITANCE







MECHANICAL AND MARKING INFORMATION LSC10065Q8





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